

IGBT for Automotive Application

1200 V, 25 A

AFGHL25T120RHD

Description

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction. Provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss, which is AEC Q101 qualified offer the optimum performance for both hard and soft switching topology in automotive application.

Features

- Extremely Efficient Trench with Field Stop Technology
- Maximum Junction Temperature: $T_J = 175^{\circ}\text{C}$
- Short Circuit Withstand Time 8 μs
- 100% of the Parts Tested for I_{LM} (Note 2)
- Fast Switching
- Tighten Parameter Distribution
- AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Typical Applications

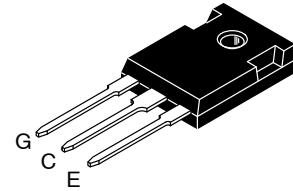
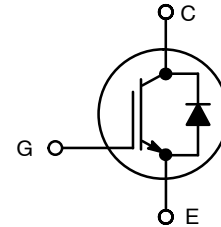
- Automotive HEV-EV e-compressor
- Automotive HEV-EV PTC heater
- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



ON Semiconductor®

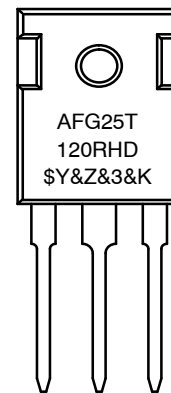
www.onsemi.com

V_{CES}	I_C	$V_{CE(Sat)}$
1200 V	25 A	2.0 V (Typ.)



TO-247-3L
CASE 340CX

MARKING DIAGRAM



AFG25T120RHD = Specific Device Code
 \$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = 3-Digit Date Code
 &K = 2-Digit Lot Traceability Code

ORDERING INFORMATION

Device	Package	Shipping
AFGHL25T120RHD	TO-247-3L	30 Units / Rail

AFGHL25T120RHD

MAXIMUM RATINGS

Description	Symbol	Value	Units
Collector to Emitter Voltage	V_{CES}	1200	V
Gate to Emitter Voltage	V_{GES}	± 20	V
Transient Gate to Emitter Voltage		± 30	
Collector Current @ $T_C = 25^\circ\text{C}$ (Note 1)	I_C	48	A
Collector Current @ $T_C = 100^\circ\text{C}$		25	
Pulsed Collector Current (Note 2)	I_{LM}	100	A
Pulsed Collector Current (Note 3)	I_{CM}	100	A
Diode Forward Current @ $T_C = 25^\circ\text{C}$ (Note 1)	I_F	48	A
Diode Forward Current @ $T_C = 100^\circ\text{C}$		25	
Pulsed Diode Maximum Forward Current	I_{FM}	100	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	261	W
Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$		130	
Short Circuit Withstand Time $V_{GE} = 15\text{ V}, V_{CE} = 600\text{ V}, T_J = 150^\circ\text{C}$	SCWT	8	μs
Operating Junction Temperature / Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Maximum Lead Temp. For Soldering Purposes, $\frac{1}{8}$ " from case for 5 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Value limited by bond wire.
- $V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 100\text{ A}, R_G = 15\ \Omega$, Inductive Load, 100% Tested
- Repetitive rating: pulse width limited by max. Junction temperature.

THERMAL CHARACTERISTICS

Rating	Symbol	Max.	Units
Thermal Resistance, Junction to Case, for IGBT	$R_{\theta JC}$	0.57	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case, Max for Diode	$R_{\theta JC}$	0.63	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient, Max	$R_{\theta JA}$	40	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

Collector-emitter Breakdown Voltage, Gate-emitter Short-circuited	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	BV_{CES}	1250	-	-	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$\frac{\Delta BV_{CES}}{\Delta T_J}$	-	1.3	-	$\text{V}/^\circ\text{C}$
Collector-emitter Cut-off Current, Gate-emitter Short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	I_{CES}	-	-	40	μA
Gate Leakage Current, Collector-emitter Short-circuited	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	± 400	nA

ON CHARACTERISTICS

Gate-emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 25\text{ mA}$	$V_{GE(th)}$	5.3	6.3	7.3	V
Collector-emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 25\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 175^\circ\text{C}$	$V_{CE(sat)}$	-	1.84 2.29	2.4 -	V

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	3920	–	pF
Output Capacitance		C_{oes}	–	157	–	
Reverse Transfer Capacitance		C_{res}	–	71	–	

SWITCHING CHARACTERISTICS

Turn-on Delay Time	$T_J = 25^\circ\text{C}$ $V_{CC} = 600\text{ V}, I_C = 12.5\text{ A}$ $R_g = 5\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	–	26	–	ns	
Rise Time		t_r	–	10	–		
Turn-off Delay Time		$t_{d(off)}$	–	133	–		
Fall Time		t_f	–	106	–		
Turn-on Switching Loss		E_{on}	–	0.9	–		mJ
Turn-off Switching Loss		E_{off}	–	0.44	–		
Total Switching Loss		E_{ts}	–	1.34	–		
Turn-on Delay Time	$T_J = 25^\circ\text{C}$ $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $R_g = 5\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	–	27	–	ns	
Rise Time		t_r	–	16	–		
Turn-off Delay Time		$t_{d(off)}$	–	118	–		
Fall Time		t_f	–	101	–		
Turn-on Switching Loss		E_{on}	–	1.94	–		mJ
Turn-off Switching Loss		E_{off}	–	0.77	–		
Total Switching Loss		E_{ts}	–	2.71	–		
Turn-on Delay Time	$T_J = 175^\circ\text{C}$ $V_{CC} = 600\text{ V}, I_C = 12.5\text{ A}$ $R_g = 5\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	–	24	–	ns	
Rise Time		t_r	–	12	–		
Turn-off Delay Time		$t_{d(off)}$	–	156	–		
Fall Time		t_f	–	280	–		
Turn-on Switching Loss		E_{on}	–	1.42	–		mJ
Turn-off Switching Loss		E_{off}	–	1.03	–		
Total Switching Loss		E_{ts}	–	2.45	–		
Turn-on Delay Time	$T_J = 175^\circ\text{C}$ $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $R_g = \text{TBD}$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	–	28	–	ns	
Rise Time		t_r	–	16	–		
Turn-off Delay Time		$t_{d(off)}$	–	132	–		
Fall Time		t_f	–	208	–		
Turn-on Switching Loss		E_{on}	–	2.87	–		mJ
Turn-off Switching Loss		E_{off}	–	1.57	–		
Total Switching Loss		E_{ts}	–	4.44	–		
Total Gate Charge	$V_{CE} = 600\text{ V}, I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	189	–	nC	
Gate to Emitter Charge		Q_{ge}	–	33	–		
Gate to collector Charge		Q_{gc}	–	97	–		

DIODE CHARACTERISTICS

Forward Voltage	$I_F = 25\text{ A}, T_J = 25^\circ\text{C}$ $I_F = 25\text{ A}, T_J = 175^\circ\text{C}$	V_F	– –	1.43 1.44	2.0 –	V
Reverse Recovery Energy	$T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}, I_F = 12.5\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s},$	E_{rec}	–	0.46	–	mJ
Diode Reverse Recovery Time		T_{rr}	–	112	–	ns
Diode Reverse Recovery Charge		Q_{rr}	–	1537	–	nC

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
DIODE CHARACTERISTICS						
Reverse Recovery Energy	$T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 25\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$,	E_{rec}	–	0.75	–	mJ
Diode Reverse Recovery Time		T_{rr}	–	159	–	ns
Diode Reverse Recovery Charge		Q_{rr}	–	2429	–	nC
Reverse Recovery Energy	$T_J = 175^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 12.5\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$,	E_{rec}	–	1.13	–	mJ
Diode Reverse Recovery Time		T_{rr}	–	185	–	ns
Diode Reverse Recovery Charge		Q_{rr}	–	3241	–	nC
Reverse Recovery Energy	$T_J = 175^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 25\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$,	E_{rec}	–	1.48	–	mJ
Diode Reverse Recovery Time		T_{rr}	–	214	–	ns
Diode Reverse Recovery Charge		Q_{rr}	–	4233	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AFGHL25T120RHD

TYPICAL CHARACTERISTICS

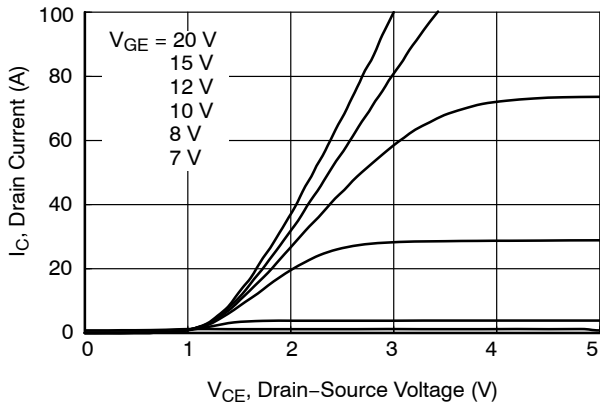


Figure 1. Typical Output Characteristics (25°C)

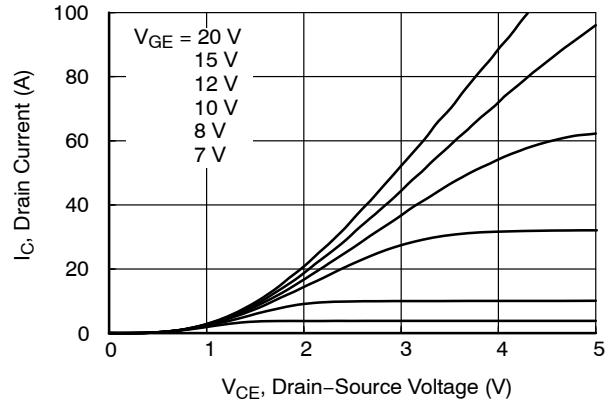


Figure 2. Typical Output Characteristics (175°C)

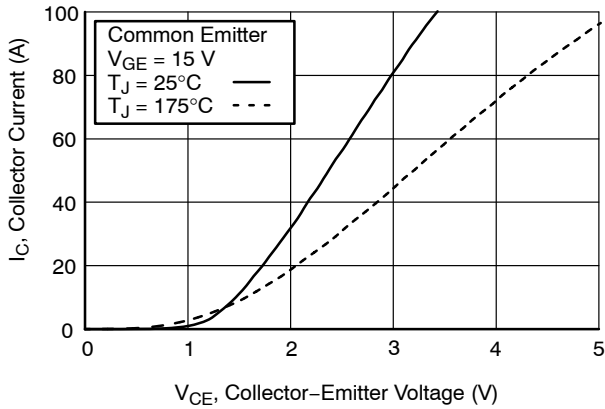


Figure 3. Typical Saturation Voltage Characteristics

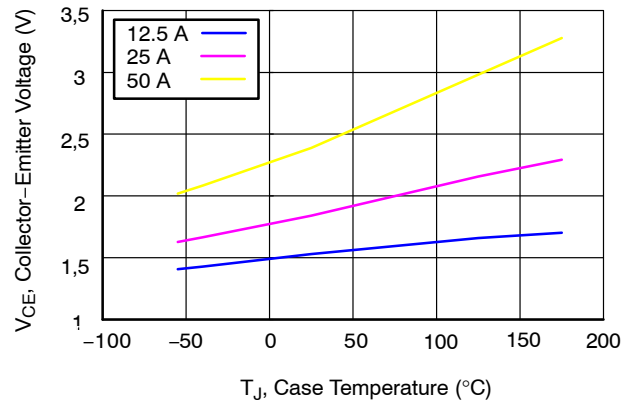


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

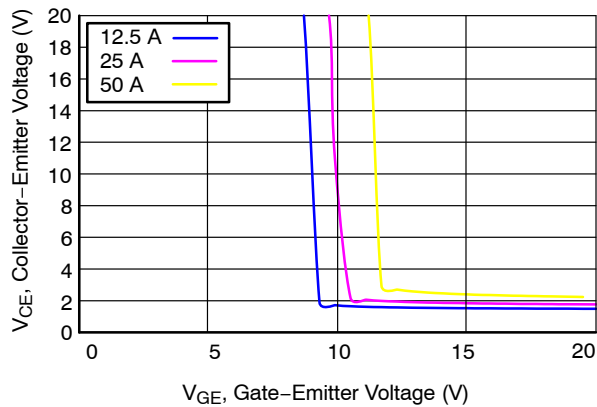


Figure 5. Saturation Voltage vs. V_{GE} (25°C)

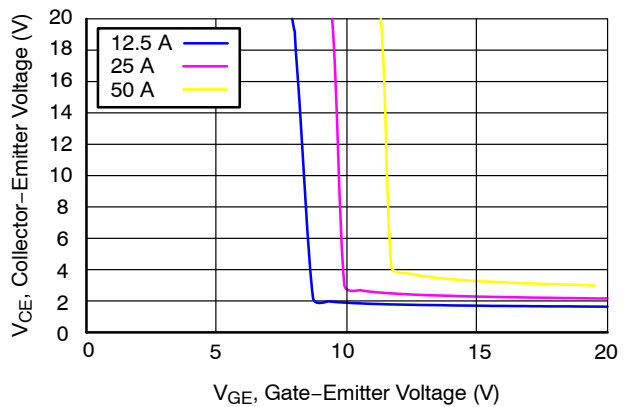


Figure 6. Saturation Voltage vs. V_{GE} (175°C)

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TYPICAL CHARACTERISTICS (continued)

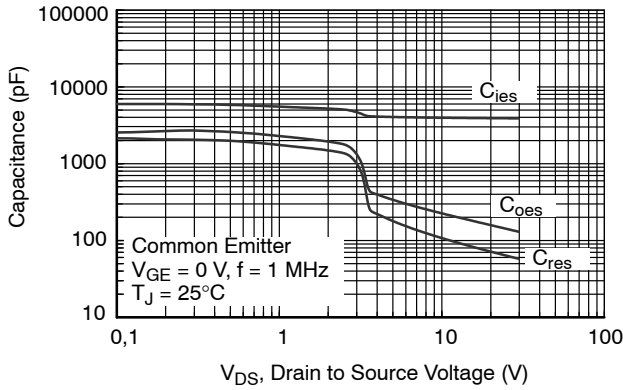


Figure 7. Capacitance Characteristics

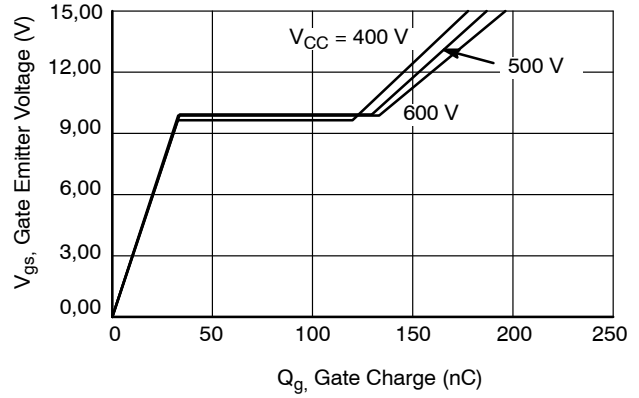


Figure 8. Gate Charge Characteristics

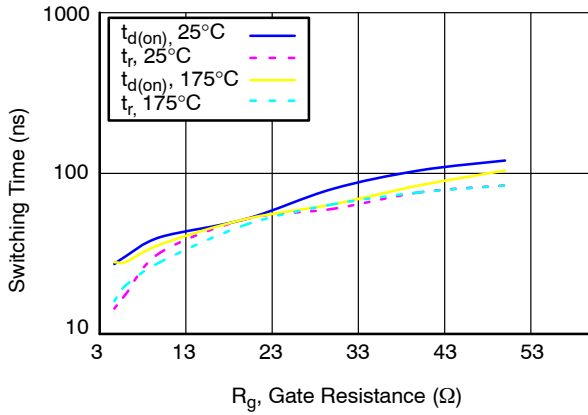


Figure 9. Turn-on Characteristics vs. Gate Resistance

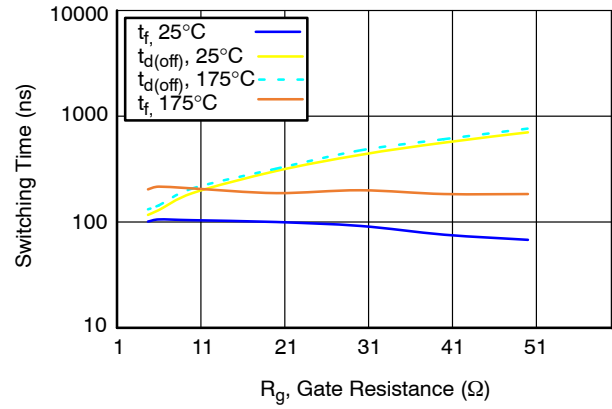


Figure 10. Turn-off Characteristics vs. Gate Resistance

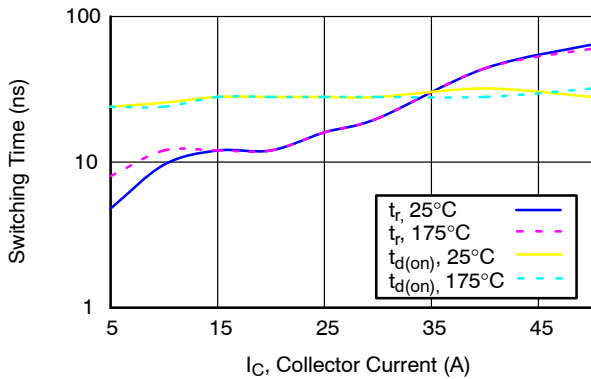


Figure 11. Turn-on Characteristics vs. Collector Current

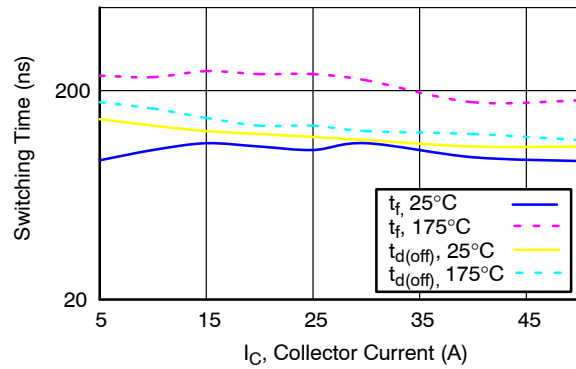


Figure 12. Turn-off Characteristics vs. Collector Current

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TYPICAL CHARACTERISTICS (continued)

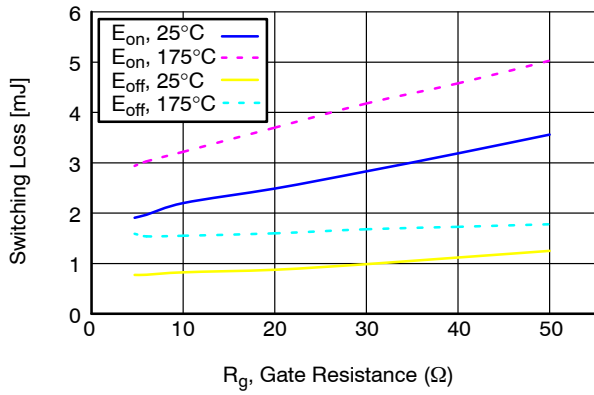


Figure 13. Switching Loss vs. Gate Resistance

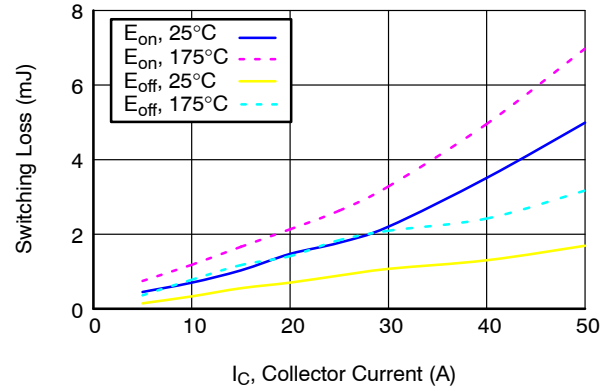


Figure 14. Switching Loss vs. Collector Current

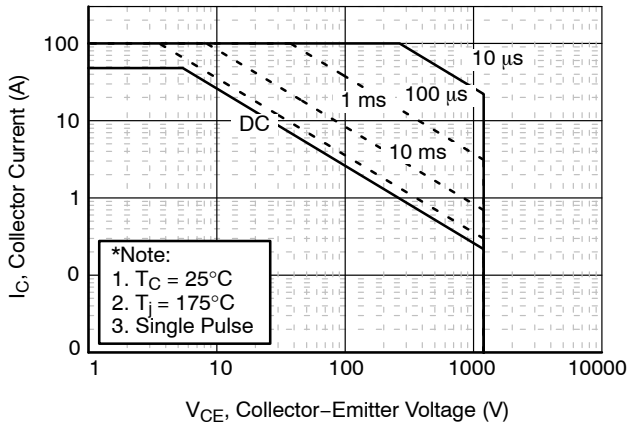


Figure 15. SOA Characteristics

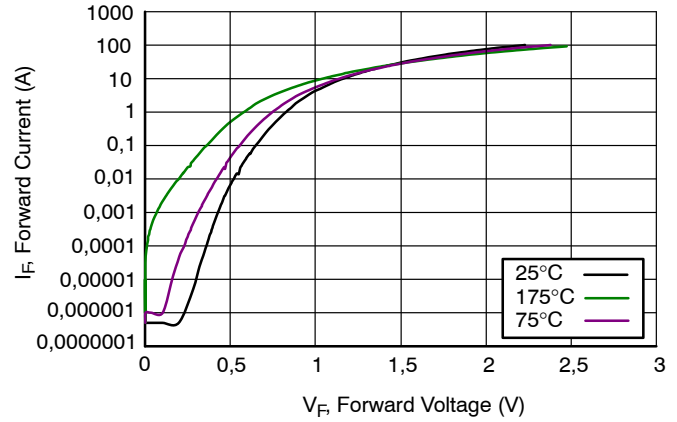


Figure 16. Forward Characteristics

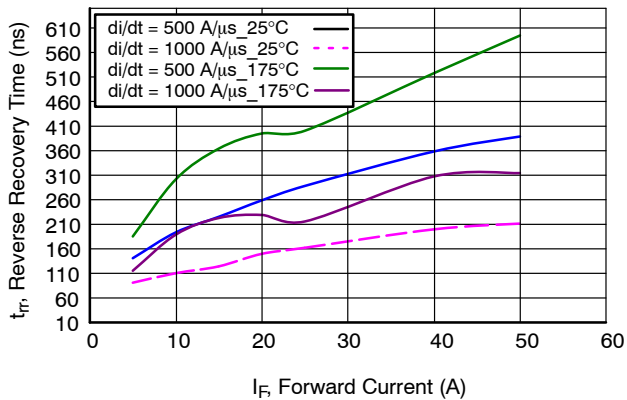


Figure 17. Reverse Recovery Time

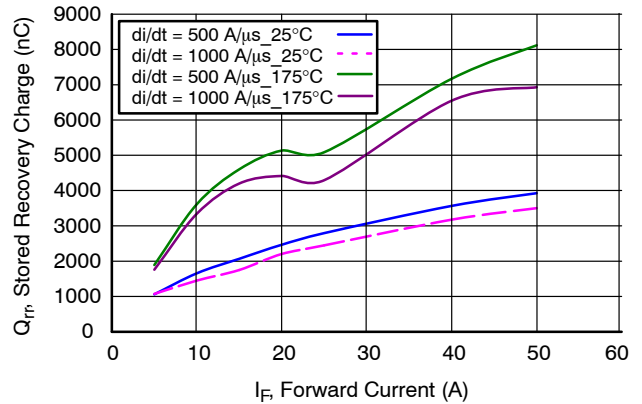


Figure 18. Stored Charge

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TYPICAL CHARACTERISTICS (continued)

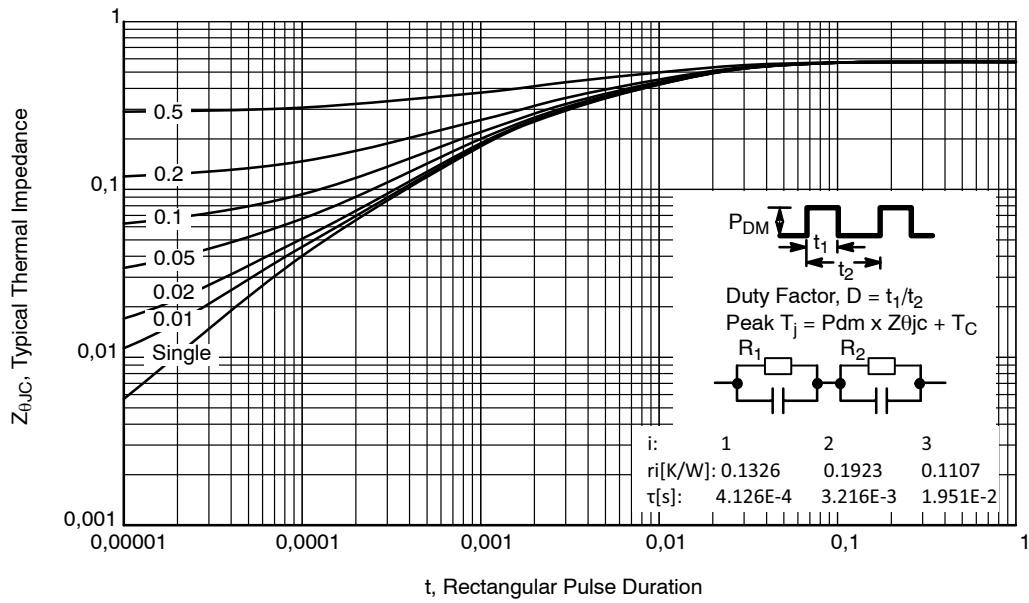


Figure 19. Transient Thermal Impedance of IGBT

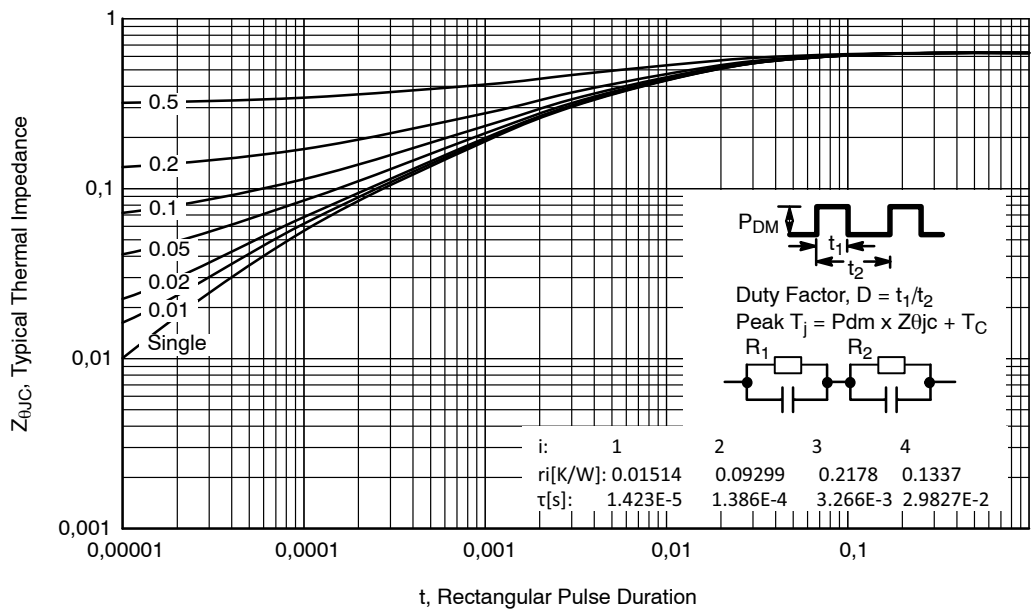


Figure 20. Transient Thermal Impedance of Diode

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Figure 21. Test Circuit for Switching Characteristics



Figure 22. Definition of Turn On Waveform

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Figure 23. Definition of Turn Off Waveform

MECHANICAL CASE OUTLINE

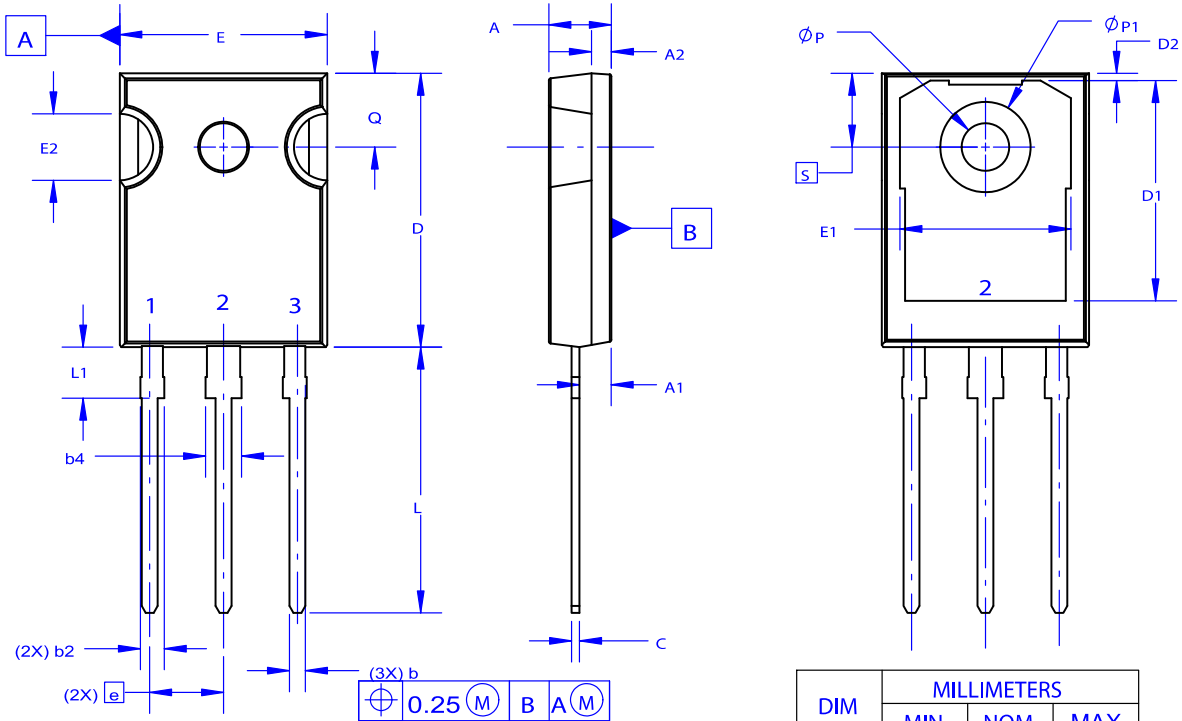
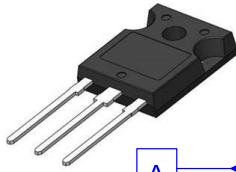
PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

GENERIC MARKING DIAGRAM*



- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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